

BDY90

MECHANICAL DATA

Dimensions in mm (inches)





NPN SILICON TRANSISTOR

FEATURES

- V_{(BR)CEO} = 100V (Min) Hermetically Sealed TO3 Metal Package
- **Screening Options Available**

APPLICATIONS

Linear & Switching • Applications

TO3 (TO-204AA)



ABSOLUTE MAXIMUM RATINGS ($T_{a} = 25^{\circ}C$ unless otherwise stated)

V _{ceo}	Collector - Emitter Voltage	100V		
V_{cev}	Collector - Emitter Voltage ($V_{BE} = -1.5V$)		120V	
V_{CBO}	Collector - Base Voltage		120V	
V_{EBO}	Emitter – Base Voltage	6V		
I _c	Collector Current - Con	10A		
	Peak		15A	
I _B	Base Current		2A	
P _D	Power Dissipation at	$T_c = 25^{\circ}C$	60W	
		Derate Above 25°C	0.4W/°C	
Т,	Junction Temperature		175°C	
T _{stg}	Storage Temperature		-65 to +175°C	

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612. E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk



THERM	AL CHARACTERISTICS	Мах	Unit
$R_{\theta_{JC}}$	Thermal resistance junction to case	2.5	°C/W

ELECTRICAL CHARACTERISTICS (T _c =25°C unless otherwise stated)								
	Parameter	Test Conditions		Min.	Тур.	Max.	Unit	
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage	$I_c = 10 \text{mA}$	$I_{\rm B} = 0$	100			V	
I _{cev}	Collector-Emitter Cut-Off Current	V _{CE} = 120V	$V_{_{BE}} = -1.5V$			1.0	mA	
			$T_c = 150^{\circ}C$			3		
I _{EBO}	Emitter-Base Cut-Off Current	$I_c = 0$	$V_{EB} = 6V$			1.0		
I _{cbo}	Collector-Base Cut-Off Current	$I_{E} = 0$	$V_{_{CB}} = 120V$			1.0		
h _{re} *	Forward-current transfer ratio	I _c = 1.0A	$V_{ce} = 2V$	30				
		I _c = 5.0A	$V_{ce} = 5V$	30		120		
		I _c = 10A	$V_{ce} = 5V$	20				
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_c = 5A$	I _B = 500mA			0.5		
		I _c = 10A	I _B = 1.0A			1.5	V	
V _{BE(sat)} *	Base-Emitter Saturated Voltage	I _c = 5A	I _B = 500mA			1.2	v	
		I _c = 10A	I _B = 1.0A			1.5		

DYNA	MIC CHARACTERISTICS					
f _T	Transition Frequency	l _c = 500mA f = 10MHz	$V_{ce} = 5V$	20		MHz
C _{obo}	Output Capacitance	l _e = 0 f = 1.0MHz	$V_{_{CB}} = 10V$		200	pF
t _{on}	Turn-On Time	$V_{cc} = 30V$ $I_c = 5A$	Ι _{в1} = 0.5Α		0.35	10
t _s	Storage Time	$V_{cc} = 30V$			1.3	μs
t,	Fall Time	I _c = 5A	$I_{_{B1}} = -I_{_{B2}} = 0.5A$		0.2	

* Pulse test $t_p = 300 \mu s$, $\delta < 2\%$

Semelab plc. Telephone +44(0)1455 556565. Fax +44(0)1455 552612. E-mail: <u>sales@semelab.co.uk</u> Website: <u>http://www.semelab.co.uk</u>

Semelab Plc reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.